

# **Excellent Integrated System Limited**

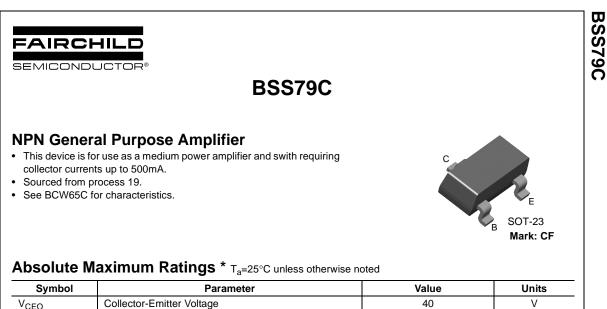
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V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	75	V
V <sub>EBO</sub>	Emitter-Base Voltage	6.0	V
I <sub>C</sub>	Collector Current - Continuous	800	mA
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 ~ +150	°C
* These ratings are lim	ting values above which the serviceability of any semiconductor device may be	impaired.	

NOTES:

These ratings are based on a maximum junction temperature of 150 degrees C.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Electrical Characteristics Ta=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charac	teristics	·			
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$	75		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \mu {\rm A}, I_{\rm E} = 0$	40		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10\mu A, I_{\rm C} = 0$	6.0		V
I <sub>CBO</sub>	Collector-Cutoff Current	$V_{CB} = 60V$ $V_{CB} = 60V, T_a = 150^{\circ}C$		10 10	nA μA
I <sub>EBO</sub>	Emitter-Cutoff Current	$V_{EB} = 3.0V, I_{C} = 0$		10	nA
On Charac	teristics *	·			
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 150mA, V <sub>CE</sub> = 10V	100	300	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{C} = 150$ mA, $I_{B} = 15$ mA $I_{C} = 500$ mA, $I_{B} = 50$ mA		0.3 1.0	V V
Small Sigr	al Characteristics	·	•		
f <sub>T</sub>	Current Gain - Bandwidth Product	I <sub>C</sub> = 20mA, V <sub>CE</sub> = 20V, f = 100MHz		250	MHz
C <sub>CB</sub>	Collector-Base Capacitance	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1.0MHz		8.0	pF
Switching	Characteristics	-			
t <sub>d</sub>	Delay Time	$V_{CC} = 30V, V_{BE(OFF)} = 0.5V,$		10	ns
t <sub>r</sub>	Rise Time	I <sub>C</sub> = 150mA, I <sub>B1</sub> = 15mA		10	ns
t <sub>s</sub>	Storage Time	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA,		265	ns
t <sub>f</sub>	Fall Time	$I_{B1} = I_{B2} = 15 \text{mA}$		60	ns

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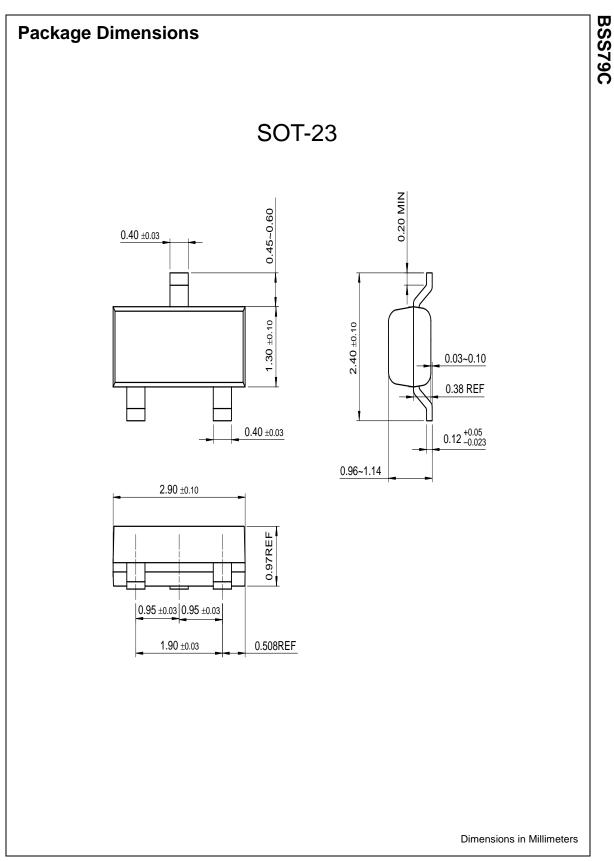


b     Total Device Dissipation     350     mW//C       Aut     Thermal Resistance, Junction to Ambient     357     °C/W       evec mounted or R44 PG8 400m × 40mm × 1.5mm     357     °C/W     ************************************	Symbol	Parameter	Max.	Units
		Total Device Dissipation	350	mW
type in the main resistance, Junction to Antolem 1 (2007) (2007) wide mounted on PR-4 PCB 400mm × 40mm × 1.5mm	<b>`</b>			
	Nevice mounted (	n FR-4 PCB 400mm × 40mm × 1.5mm	557	C/W

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Rev. A, June 2004





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ACEx™	FAST <sup>®</sup>	ISOPLANAR™	Power247™	SuperFET™
ActiveArray™	FASTr™	LittleFET™	PowerSaver™	SuperSOT™-3
Bottomless™	FPS™	MICROCOUPLER™	PowerTrench <sup>®</sup>	SuperSOT™-6
CoolFET™	FRFET™	MicroFET™	QFET <sup>®</sup>	SuperSOT™-8
CROSSVOLT™	GlobalOptoisolator™	MicroPak™	QS™	SyncFET™
DOME™	GTO™	MICROWIRE™	QT Optoelectronics™	TinyLogic®
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E <sup>2</sup> CMOS™	I <sup>2</sup> C™	MSXPro™	RapidConfigure™	TruTranslation <sup>⊤</sup>
EnSigna™	<i>i-Lo</i> ™	OCX™	RapidConnect™	UHC™
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